



# STP75NF75L STB75NF75L STB75NF75L-1

N-CHANNEL 75V - 0.009  $\Omega$  - 75A D<sup>2</sup>PAK/I<sup>2</sup>PAK/TO-220  
STripFET™ II POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB75NF75L/-1	75 V	<0.011 $\Omega$	75 A
STP75NF75L	75 V	<0.011 $\Omega$	75 A

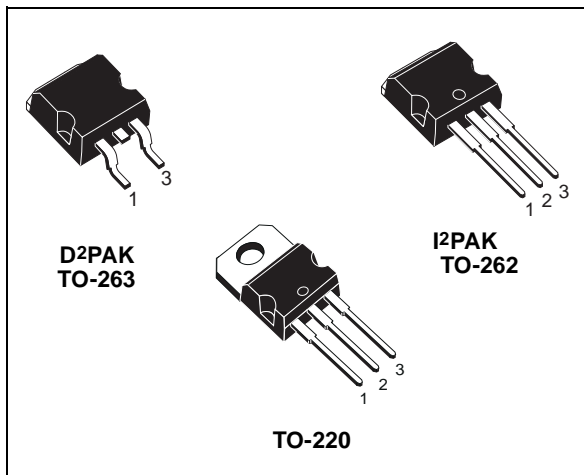
- TYPICAL R<sub>DS(on)</sub> = 0.009 $\Omega$
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW THRESHOLD DRIVE

## DESCRIPTION

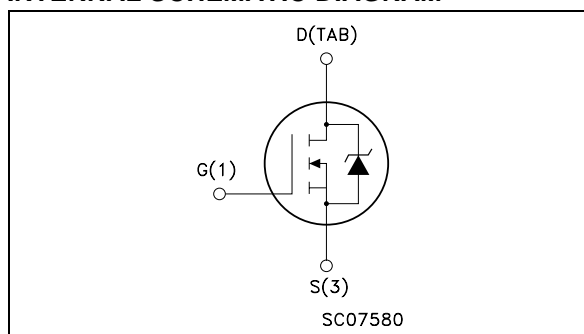
This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

## APPLICATIONS

- SOLENOID AND RELAY DRIVERS
- DC MOTOR CONTROL
- DC-DC CONVERTERS
- AUTOMOTIVE ENVIRONMENT



## INTERNAL SCHEMATIC DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	75	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 k $\Omega$ )	75	V
V <sub>GS</sub>	Gate- source Voltage	$\pm 15$	V
I <sub>D</sub> (●)	Drain Current (continuous) at T <sub>C</sub> = 25°C	75	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	70	A
I <sub>DM</sub> (●●)	Drain Current (pulsed)	300	A
P <sub>tot</sub>	Total Dissipation at T <sub>C</sub> = 25°C	300	W
	Derating Factor	2	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	20	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	680	mJ
T <sub>stg</sub>	Storage Temperature	-55 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature		

(●) Current limited by package

(●●) Pulse width limited by safe operating area.

(1) I<sub>SD</sub>  $\leq$  75A, di/dt  $\leq$  500A/ $\mu$ s, V<sub>DD</sub>  $\leq$  V<sub>(BR)DSS</sub>, T<sub>j</sub>  $\leq$  T<sub>JMAX</sub>.

(2) Starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = 37.5A, V<sub>DD</sub> = 30V

**STB75NF75L/-1 STP75NF75L****THERMAL DATA**

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	0.5	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose	Typ	300	°C

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 µA V <sub>GS</sub> = 0	75			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>C</sub> = 125°C			1 10	µA µA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 15 V			±100	nA

**ON (\*)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 µA	1		2.5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 37.5 A V <sub>GS</sub> = 5 V I <sub>D</sub> = 37.5 A		0.009 0.010	0.011 0.013	Ω Ω

**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> = 15 V I <sub>D</sub> = 37.5 A		120		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		4300 660 205		pF pF pF

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 40\text{ V}$ $I_D = 37.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		35 150		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 60\text{ V}$ $I_D = 75\text{ A}$ $V_{GS} = 5\text{ V}$		75 18 31	90	nC nC nC

**SWITCHING OFF**

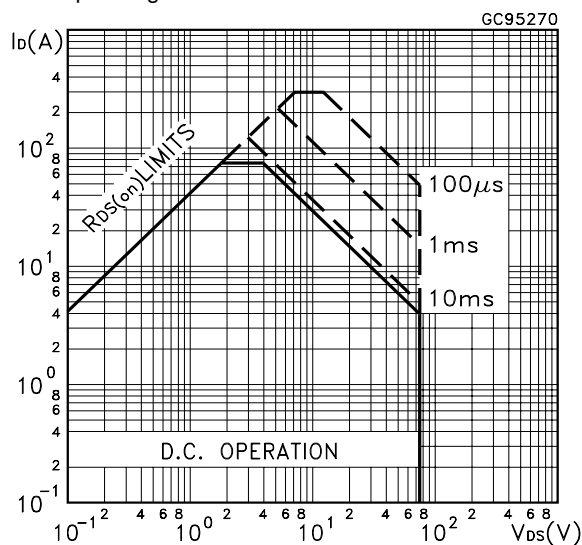
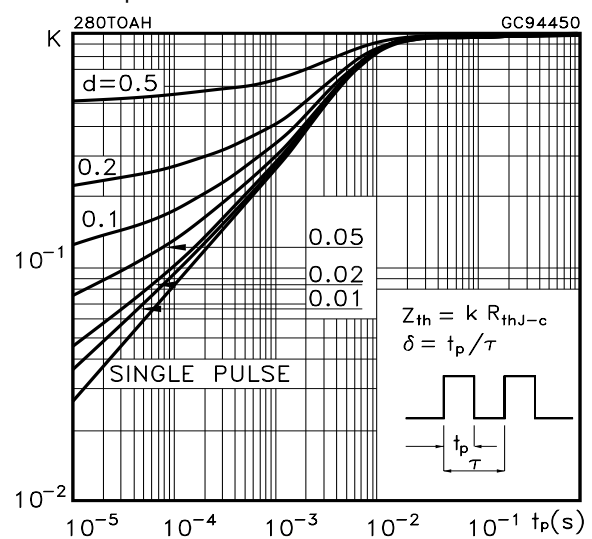
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 40\text{ V}$ $I_D = 37.5\text{ A}$ $R_G = 4.7\ \Omega$ , $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		110 60		ns ns

**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(*)}$	Source-drain Current Source-drain Current (pulsed)				75 300	A A
$V_{SD}^{(*)}$	Forward On Voltage	$I_{SD} = 75\text{ A}$ $V_{GS} = 0$			1.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 75\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		100 380 7.5		ns nC A

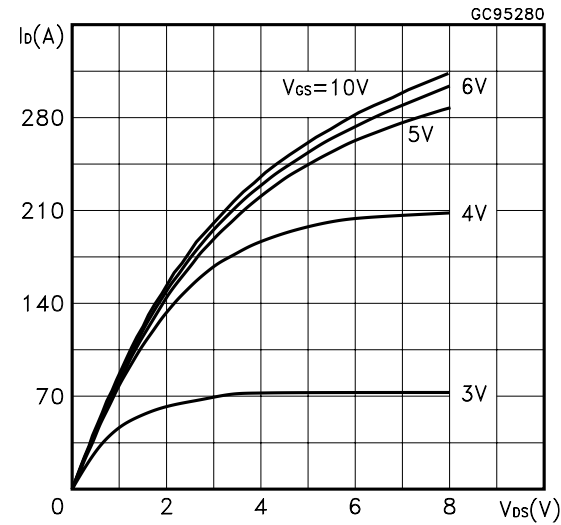
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

(●) Pulse width limited by safe operating area.

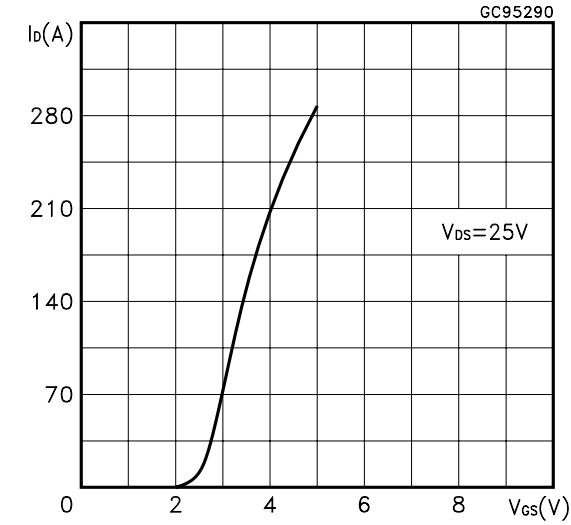
**Safe Operating Area****Thermal Impedance**

**STB75NF75L/-1 STP75NF75L**

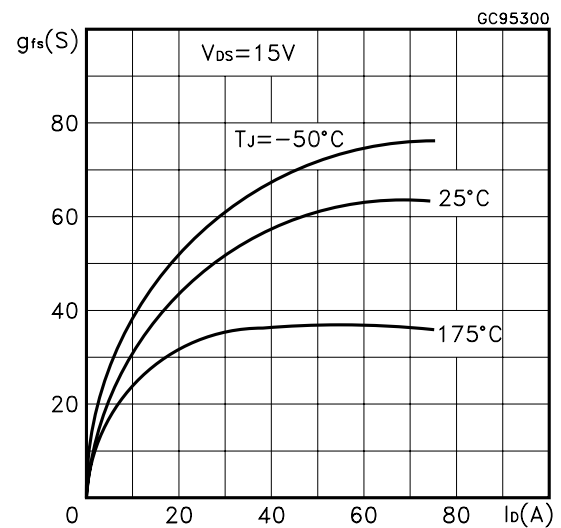
Output Characteristics



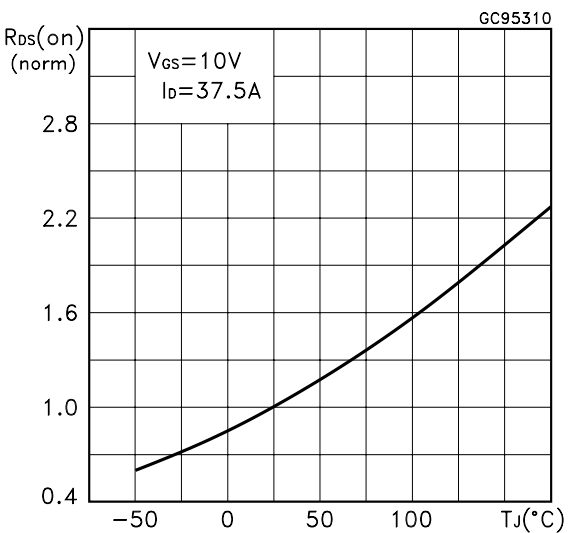
Transfer Characteristics



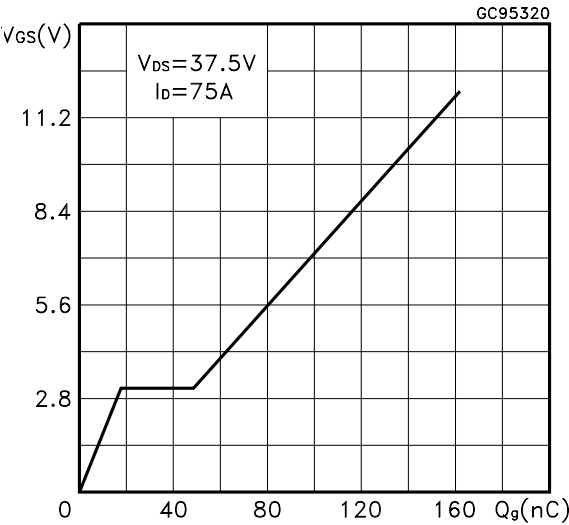
Transconductance



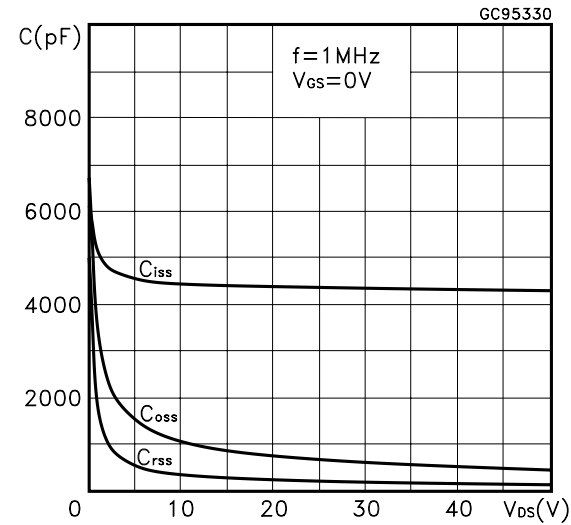
Static Drain-source On Resistance



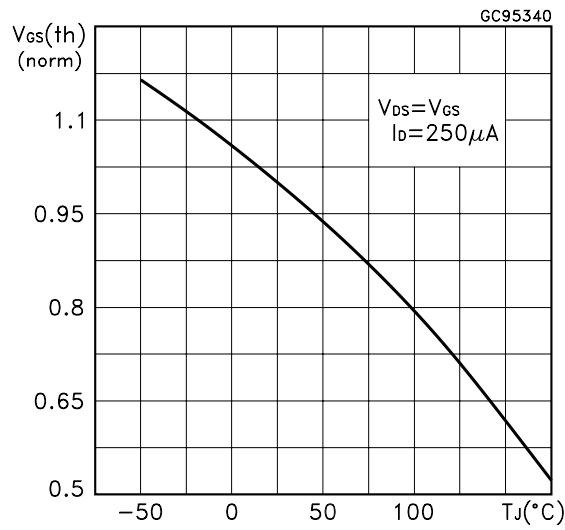
Gate Charge vs Gate-source Voltage



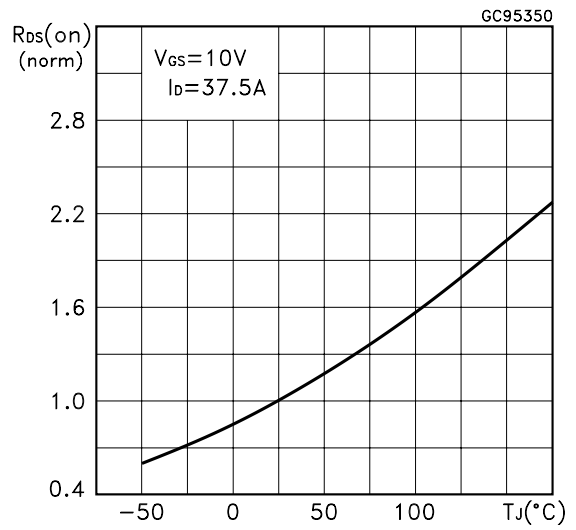
Capacitance Variations



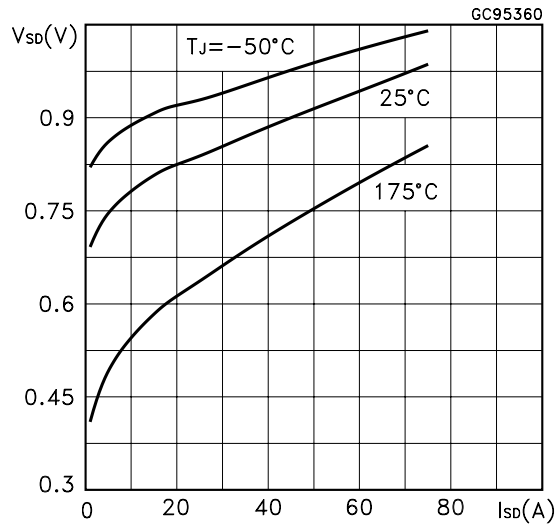
Normalized Gate Threshold Voltage vs Temperature



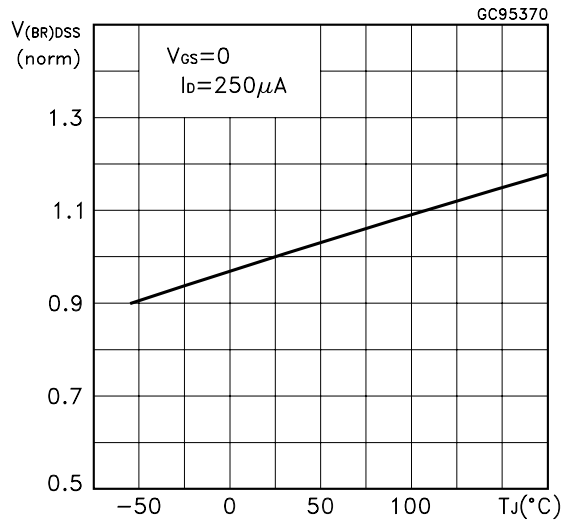
Normalized on Resistance vs Temperature



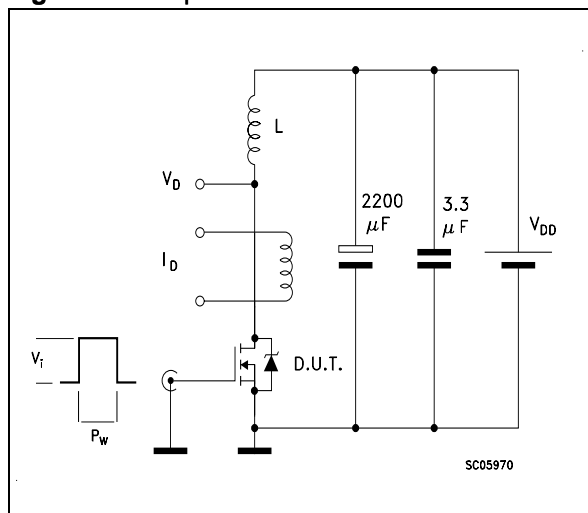
Source-drain Diode Forward Characteristics



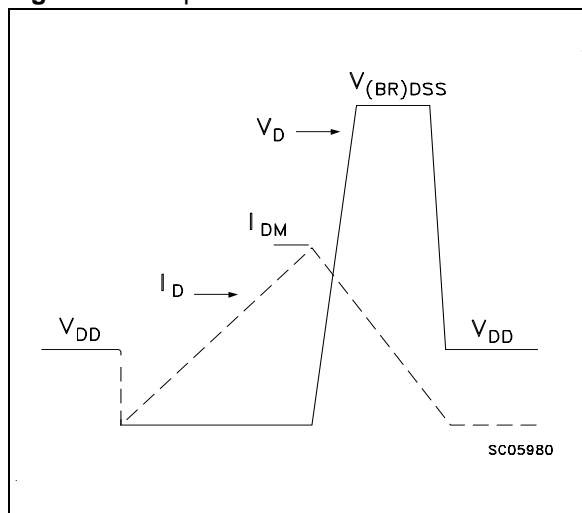
Normalized Breakdown Voltage vs Temperature.



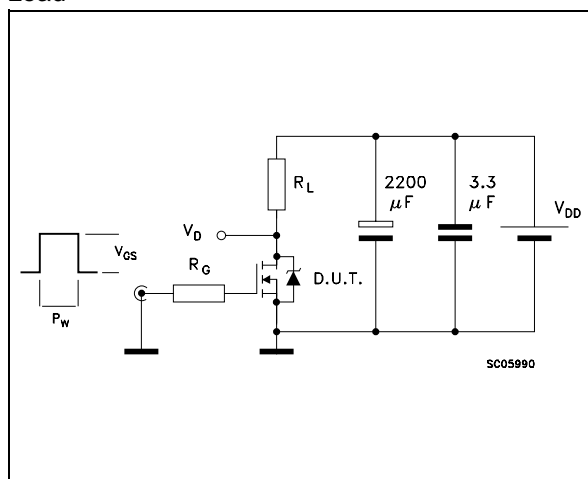
**Fig. 1: Unclamped Inductive Load Test Circuit**



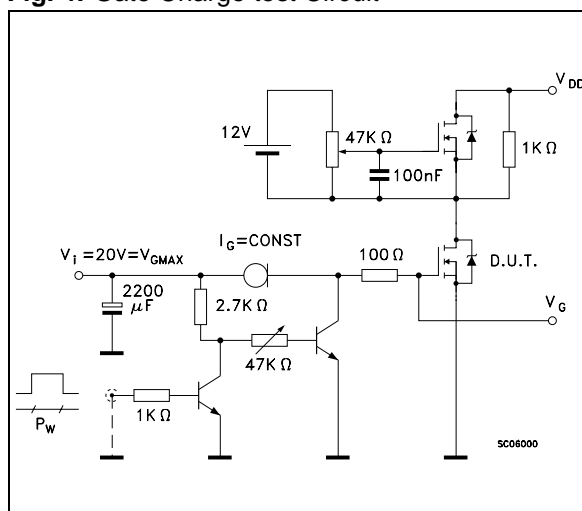
**Fig. 2: Unclamped Inductive Waveform**



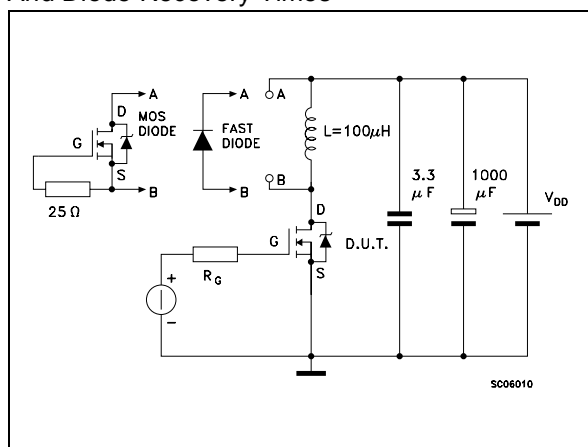
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

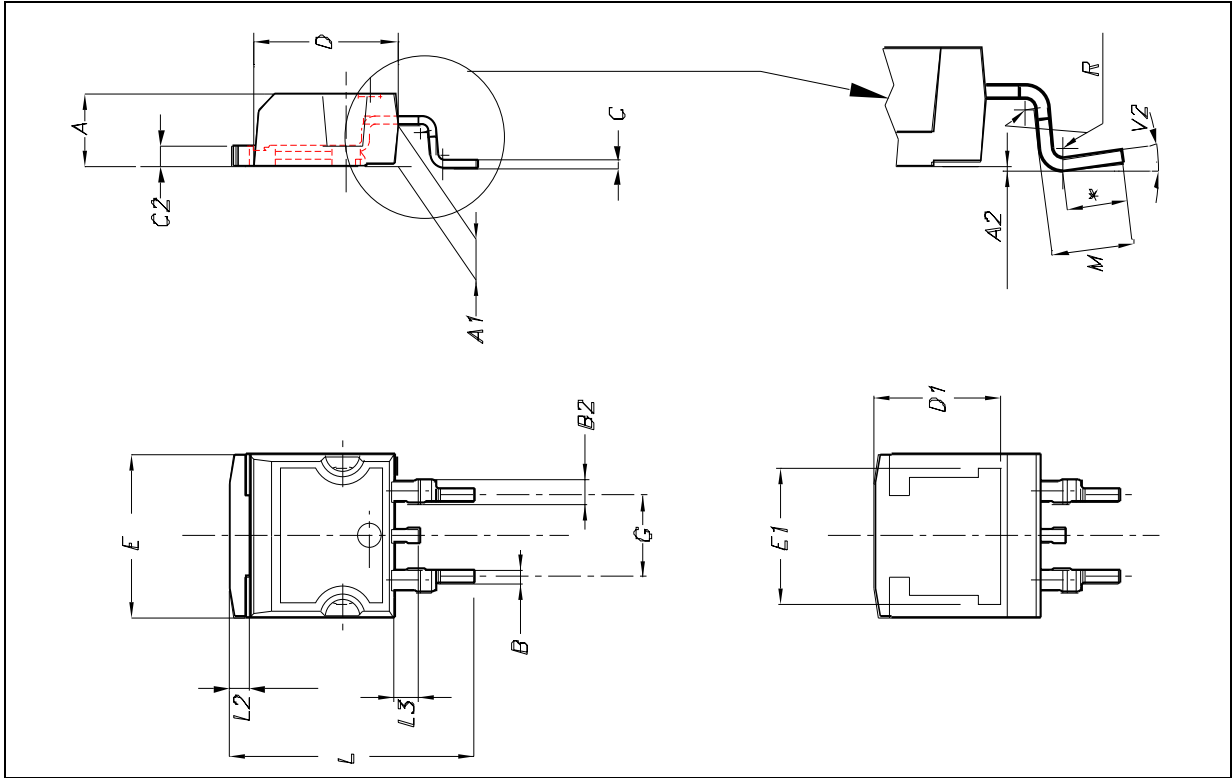


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



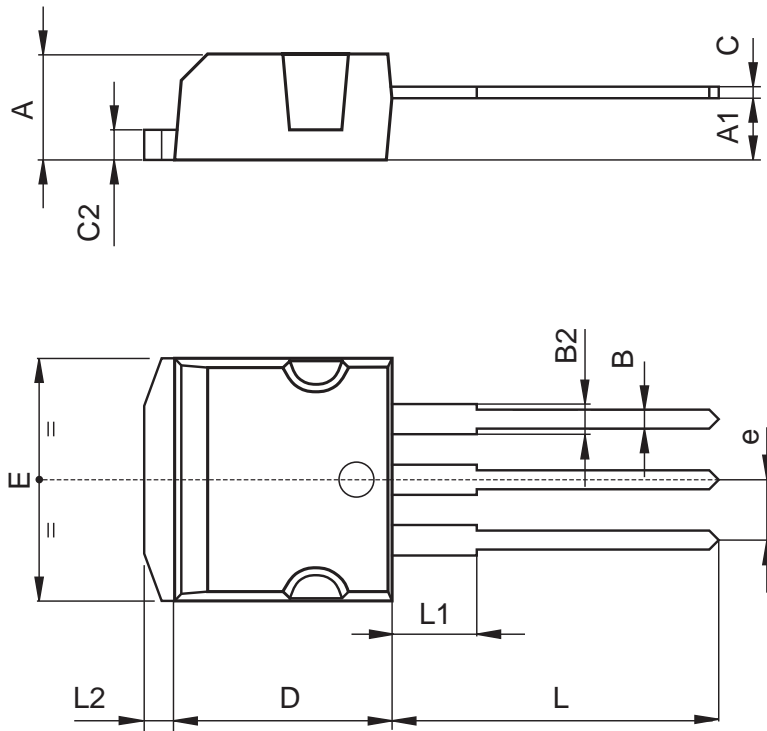
D<sup>2</sup>PAK MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1	8.5				0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.016	
V2	0°		8°	0°		8°



TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055

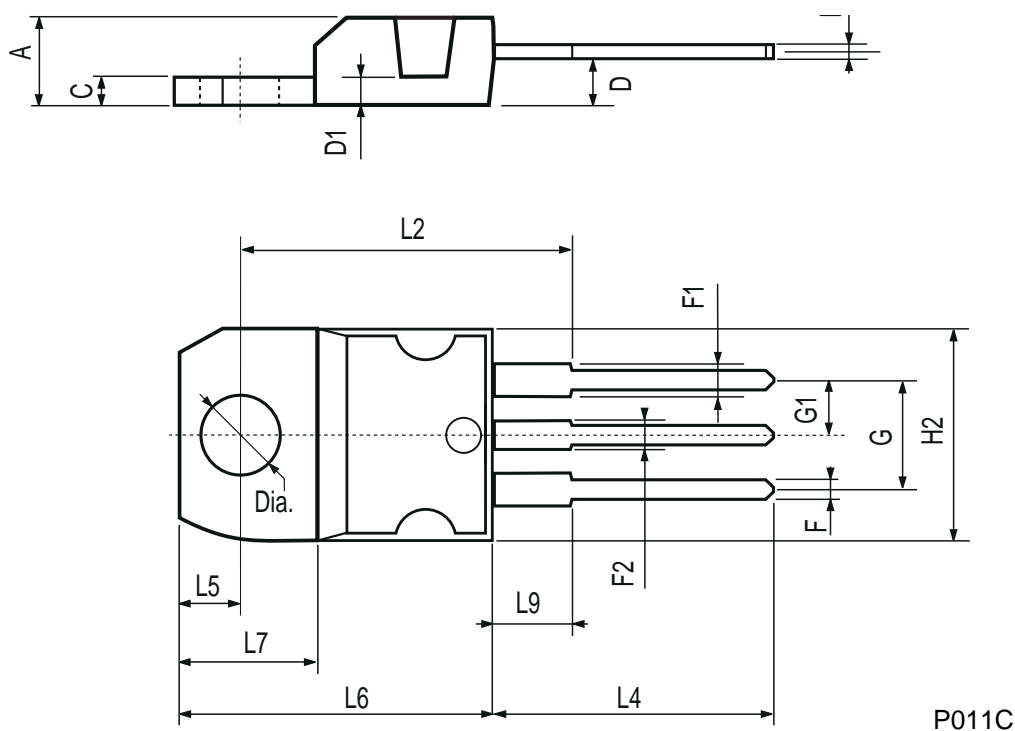


P011P5/E



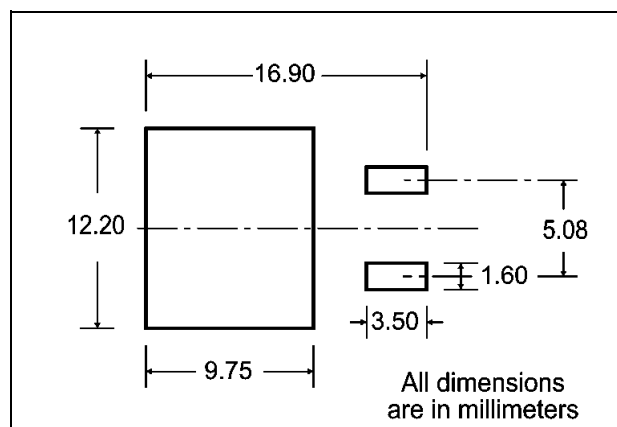
## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151

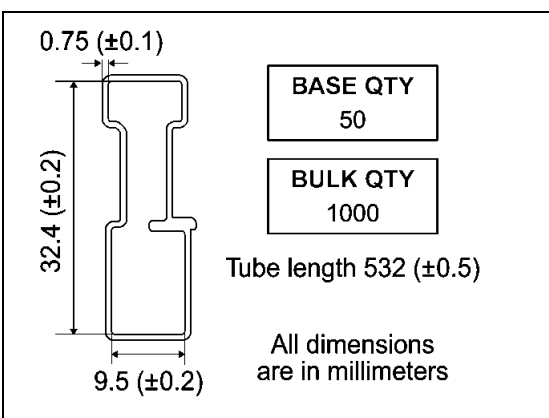


P011C

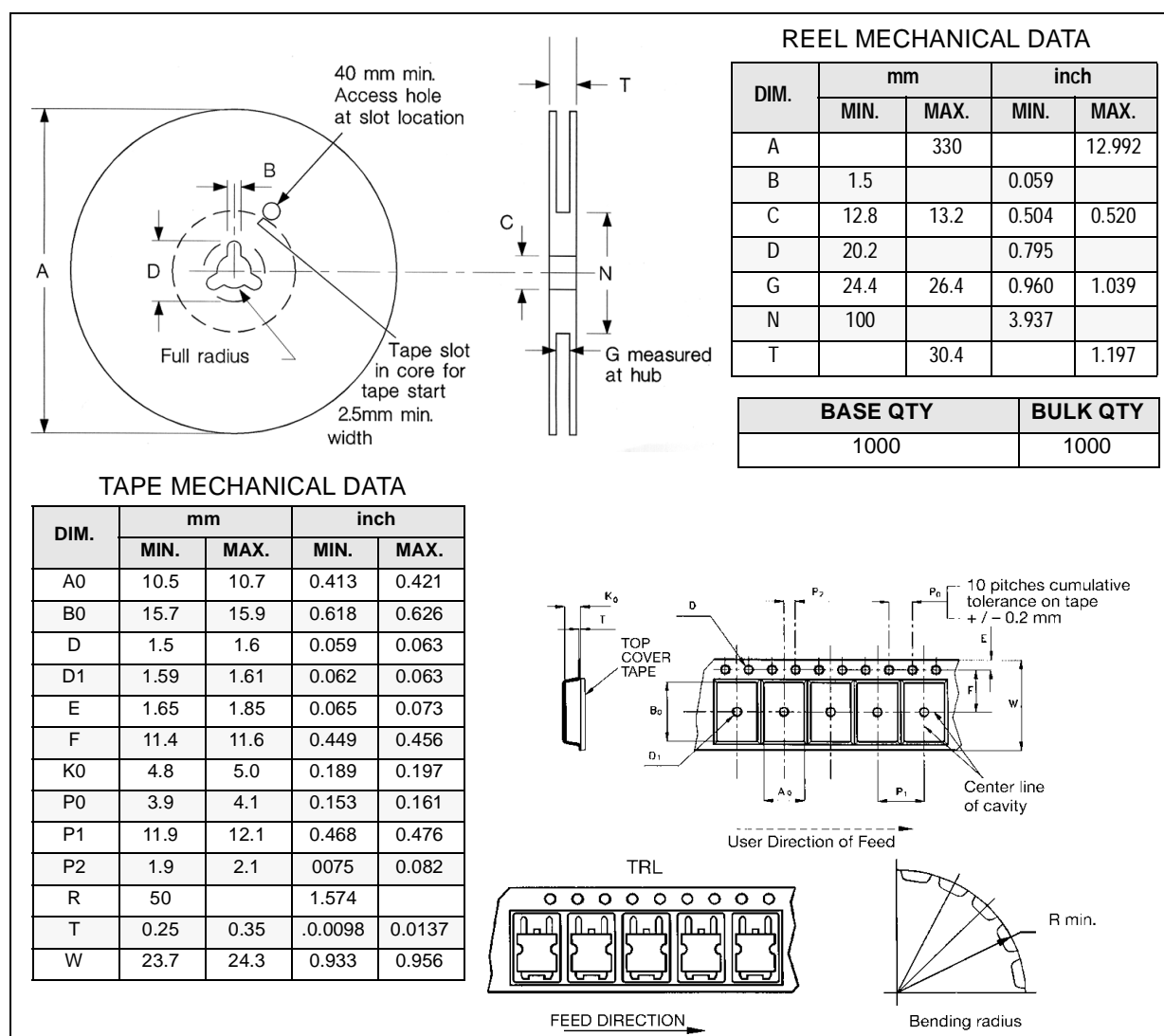
## D2PAK FOOTPRINT



## TUBE SHIPMENT (no suffix)\*



## TAPE AND REEL SHIPMENT (suffix "T4")\*



\* on sales type

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